

Form 1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1897	SERIAL NO. 10/050,347
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Gurtej S. Sandhu et al.	
FILING DATE January 15, 2002		GROUP Unknown	

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PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
RL	AA	6,255,703 B1	07/01	Hause et al.			
RL	AB	6,274,442 B1	08/01	Gardner et al.			
RL	AC	6,228,701 B1	05/01	Dehm et al.			
RL	AD	6,136,636	10/00	Wu			
RL	AE	6,033,998	03/00	Aronowitz et al.			
RL	AF	6,057,220	05/00	Ajmera et al.			
RL	AG	6,087,229	07/00	Aronowitz et al.			
RL	AH	5,998,253	12/99	Loh et al.			
RL	AI	5,763,922	06/98	Chau			
RL	AJ	6,225,167 B1	05/01	Yu et al.			
RL	AK	5,960,289	09/99	Tsui et al.			
	AL						

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AM							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
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EXAMINER <i>hanna Schiller</i>	DATE CONSIDERED <i>6/25/02</i>
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1897	SERIAL NO. 09/633,556		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.			
				FILING DATE August 7, 2000	GROUP 2813		
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,091,109	07/00	Hasegawa			
	AB	6,080,682	06/00	Ibok			
	AC	5,685,949	11/97	Yashima			
	AD	6,268,296 B1	07/01	Misium et al.			
	AE	6,232,244 B1	05/01	Ibok			
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1897	SERIAL NO. 09/633,556			
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.				
				FILING DATE August 7, 2000	GROUP 2813			
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
Per M	AA	5,760,475	06/98	Cronin				
	AB	5,834,372	11/98	Lee				
	AC	5,619,057	04/98 X	Komatsu				
	AD	5,633,036	05/97	Seebauer et al.				
	AE	6,054,396	04/00	Doan				
	AF	6,174,821	01/01	Doan				
	AG	5,939,750	08/99	Early				
	AH	5,254,489	10/93	Nakata				
	AI	5,464,792	11/95	Tseng et al.				
	AJ	5,620,908	04/97	Inoh et al.				
	AK	5,716,864	02/98	Abe				
	AL	5,972,783	10/99	Arai et al.				
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		Document Number	Date	Country	Class	Subclass	Translation	
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	AR		Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Vol. 16 (7), July 1995, pp. 301-302.					
	AS		Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+ Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.					
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EXAMINER <i>Harsha S. Seltzer</i>				DATE CONSIDERED <i>1/25/02</i>				
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[Handwritten initials]</i>	AA	5,032,545	07/91	Doan et al.	7			
<i>[Handwritten initials]</i>	AB	5,436,481	07/95	Egawa et al.				
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<i>[Handwritten initials]</i>	AD	5,258,333	11/93	Shappir et al.				
<i>[Handwritten initials]</i>	AE	5,518,946	05/96	Kuroda				
<i>[Handwritten initials]</i>	AF	5,445,999	08/95	Thakur et al.				
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<i>[Handwritten initials]</i>	AL	5,719,083	06/98	Komatsu				
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<i>[Handwritten initials]</i>	AM	WO 96/39713	12/96	PCI			Yes	No
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<i>[Handwritten initials]</i>	AR		Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 212-213.					
<i>[Handwritten initials]</i>	AS		Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 188-189, 194-195, 609-614.					
<i>[Handwritten initials]</i>	AT		Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.					
EXAMINER				DATE CONSIDERED				
<i>[Handwritten signature: Waseem Schell]</i>				6/25/02				
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